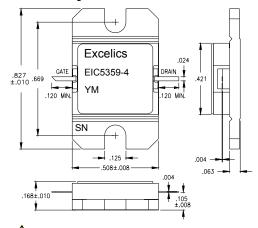


ISSUED 5/15/2006

5.3-5.9 GHz 4-Watt Internally Matched Power FET

FEATURES

- 5.3– 5.9GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +36.5 dBm Output Power at 1dB Compression
- 10.5 dB Power Gain at 1dB Compression
- 34% Power Added Efficiency
- Hermetic Metal Flange Package



Caution! ESD sensitive device.

EIC5359-4

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

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SYMBOL	PARAMETERS/TEST CONDITIONS ¹		TYP	MAX	UNITS
P _{1dB}	Output Power at 1dB Compressionf = 5.3-5.9GHz V_{DS} = 10 V, $I_{DSQ} \approx 1100$ mA	35.5	36.5		dBm
G _{1dB}		9.5	10.5		dB
∆G	$ \begin{array}{ll} \mbox{Gain Flatness} & \mbox{f} = 5.3\text{-}5.9\mbox{GHz} \\ \mbox{V}_{DS} = 10 \mbox{ V}, \mbox{I}_{DSQ} \approx 1100\mbox{mA} \end{array} $			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression V_{DS} = 10 V, $I_{DSQ} \approx 1100$ mAf = 5.3-5.9GHz		34		%
Id _{1dB}	Drain Current at 1dB Compression f = 5.3-5.9GHz		1200	1400	mA
IM3	Output 3rd Order Intermodulation Distortion Δf =10MHz 2-Tone Test. Pout=25.5 dBm S.C.LVds = 10 V, I _{DSQ} ≈ 65% I _{DSS} f = 5.9GHz	-43	-46		dBc
I _{DSS}	Saturated Drain Current V_{DS} = 3 V, V_{GS} = 0 V		2000	2500	mA
VP	Pinch-off Voltage V_{DS} = 3 V, I_{DS} = 20 mA		-2.5	-4.0	V
R _{TH}	Thermal Resistance ³		5.5	6	°C/W

Note: 1) Tested with 100 Ohm gate resistor. 2) S.C.L. = Single Carrier Level. 3) Ov

3) Overall Rth depends on case mounting.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
Vds	Drain-Source Voltage	15	10V
Vgs	Gate-Source Voltage	-5	-4V
lgsf	Forward Gate Current	43.2mA	14.4mA
lgsr	Reserve Gate Current	-7.2mA	-2.4mA
Pin	Input Power	35.5dBm	@ 3dB Compression
Tch	Channel Temperature	175 °C	175 °C
Tstg	Storage Temperature	-65 to +175 °C	-65 to +175 °C
Pt	Total Power Dissipation	25W	25W

Note: 1. Exceeding any of the above ratings may result in permanent damage. 2. Exceeding any of the above ratings may reduce MTTF below design goals.